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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8358zqaddda

  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
  - System initialization data is optionally loaded from I^2C-1 EPROM by boot sequencer embedded hardware
- DMA controller
  - Four independent virtual channels
  - Concurrent execution across multiple channels with programmable bandwidth control
  - All channels accessible by local core and remote PCI masters
  - Misaligned transfer capability
  - Data chaining and direct mode
  - Interrupt on completed segment and chain
  - DMA external handshake signals: $\overline{\text{DMA\_DREQ}}$[0:3]/$\overline{\text{DMA\_DACK}}$[0:3]/$\overline{\text{DMA\_DONE}}$[0:3]. There is one set for each DMA channel. The pins are multiplexed to the parallel IO pins with other QE functions.
- DUART
  - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- System timers
  - Periodic interrupt timer
  - Real-time clock
  - Software watchdog timer
  - Eight general-purpose timers
- IEEE Std. 1149.1™-compliant, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8358E. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode)[1]	GV_{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)[1]	GV_{DD} = 1.8 V
10/100/1000 Ethernet signals	42	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V LV_{DD} = 2.5/3.3 V

[1] DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8358E.

2.2.1 Power-Up Sequencing

MPC8358E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

Table 12. QUICC Engine Block Operating Frequency Limitations (continued)

Interface	Interface Operating Frequency (MHz)	Max Interface Bit Rate (Mbps)	Min QUICC Engine Operating Frequency[1] (MHz)	Notes
UART/async HDLC	3.68 (max internal ref clock)	115 (Kbps)	20	—
BISYNC	2 (max)	2	20	—
USB	48 (ref clock)	12	96	—

Notes:
1. The QUICC Engine module needs to run at a frequency higher than or equal to what is listed in this table.
2. 'F' is the actual interface operating frequency.
3. The bit rate limit is independent of the data bus width (that is, the same for serial, nibble, or octal interfaces).
4. TDM in high-speed mode for serial data interface.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR and DDR2 SDRAM interface of the MPC8358E.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

Table 13 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.9	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in ¼ applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
8. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.

Figure 6 shows the DDR SDRAM output timing for address skew with respect to any MCK.

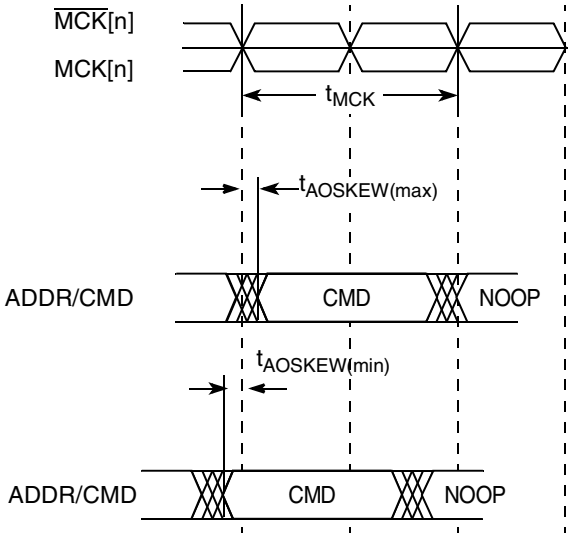


Figure 6. Timing Diagram for t_{AOSKEW} Measurement

Table 25. RGMII/RTBI DC Electrical Characteristics (when operating at 2.5 V)

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input current	I_{IN}	$0 V \le V_{IN} \le LV_{DD}$		—	±10	μA

8.2 GMII, MII, RMII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This sections describe the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 26 provides the GMII transmit AC timing specifications.

Table 26. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX} t_{GTKHDV}	0.5 —	—	— 5.0	ns	—
GTX_CLK clock rise time, (20% to 80%)	t_{GTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{GTXF}	—	—	1.0	ns	—
GTX_CLK125 clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $LV_{DD/2}$	t_{G125H}/t_{G125}	45	—	55	%	2

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Figure 13 shows the MII receive AC timing diagram.

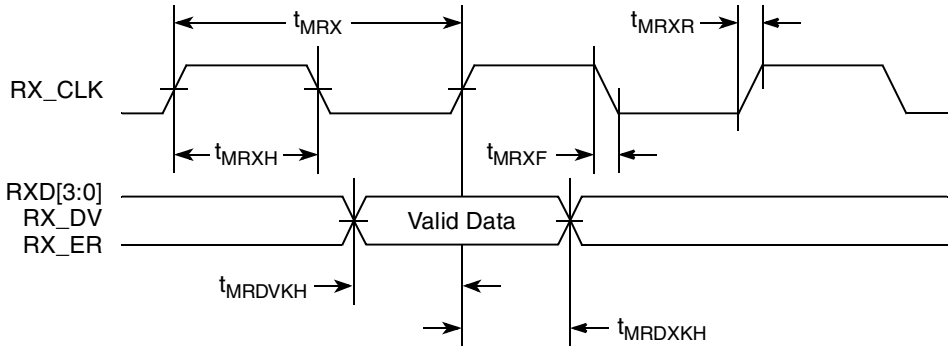


Figure 13. MII Receive AC Timing Diagram

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

Table 30 provides the RMII transmit AC timing specifications.

Table 30. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDV}$	2 —	—	— 10	ns
REF_CLK data clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 14 shows the RMII transmit AC timing diagram.

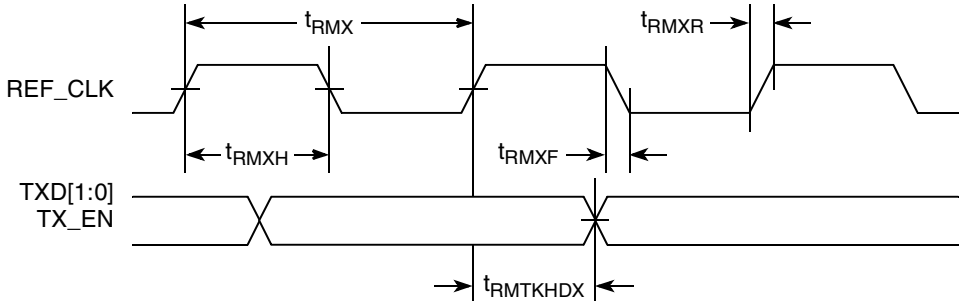


Figure 14. RMII Transmit AC Timing Diagram

8.2.3.2 RMII Receive AC Timing Specifications

Table 31 provides the RMII receive AC timing specifications.

Table 31. RMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
REF_CLK clock period	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	$t_{RMRDVKH}$	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	$t_{RMRDXKH}$	2.0	—	—	ns
REF_CLK clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMRDVKH}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, $t_{RMRDXKL}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 15 provides the AC test load.

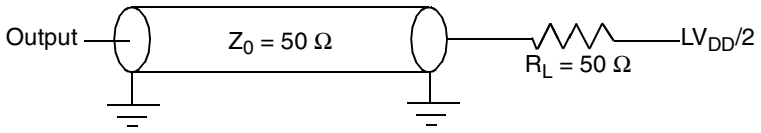


Figure 15. AC Test Load

Figure 18 shows the TBI receive AC timing diagram.

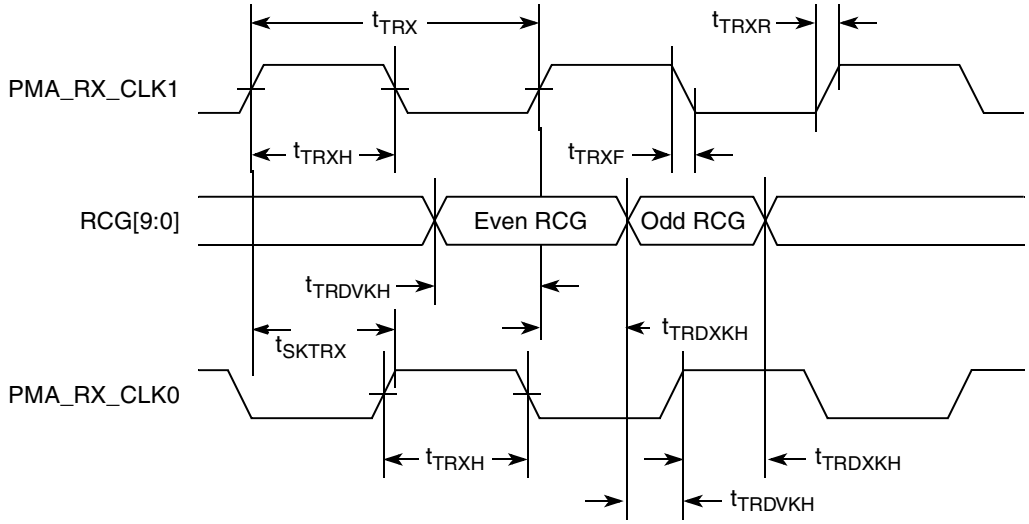


Figure 18. TBI Receive AC Timing Diagram

8.2.5 RGMII and RTBI AC Timing Specifications

Table 34 presents the RGMII and RTBI AC timing specifications.

Table 34. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
Data to clock output skew (at transmitter)	$t_{SKRGTKHDX}$ $t_{SKRGTKHDV}$	–0.5 —	—	— 0.5	ns	
Data to clock input skew (at receiver)	$t_{SKRGDXKH}$ $t_{SKRGDVKH}$	1.1 —	—	— 2.6	ns	2
Clock cycle duration	t_{RGT}	7.2	8.0	8.8	ns	3
Duty cycle for 1000Base-T	t_{RGTH}/t_{RGT}	45	50	55	%	4, 5
Duty cycle for 10BASE-T and 100BASE-TX	t_{RGTH}/t_{RGT}	40	50	60	%	3, 5
Rise time (20–80%)	t_{RGTR}	—	—	0.75	ns	—
Fall time (20–80%)	t_{RGTF}	—	—	0.75	ns	—
GTX_CLK125 reference clock period	t_{G125}	—	8.0	—	ns	6

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (10/100/1000 Mbps)— GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 35.

Table 35. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.10	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±10	μA

8.3.2 MII Management AC Electrical Specifications

Table 36 provides the MII management AC timing specifications.

Table 36. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	$t_{MDTKHDX}$ $t_{MDTKHDV}$	10 —	—	— 110	ns	3
MDIO to MDC setup time	$t_{MDRDVKH}$	10	—	—	ns	—
MDIO to MDC hold time	$t_{MDRDXKH}$	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—

Table 39. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1.0	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	1.0	—	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to rising edge of LSYNC_IN.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

Table 40 describes the general timing parameters of the local bus interface of the device.

Table 40. Local Bus General Timing Parameters—DLL Bypass Mode

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to output valid	t_{LBKHOV}	—	3	ns	3

Figure 32 provides the test access port timing diagram.

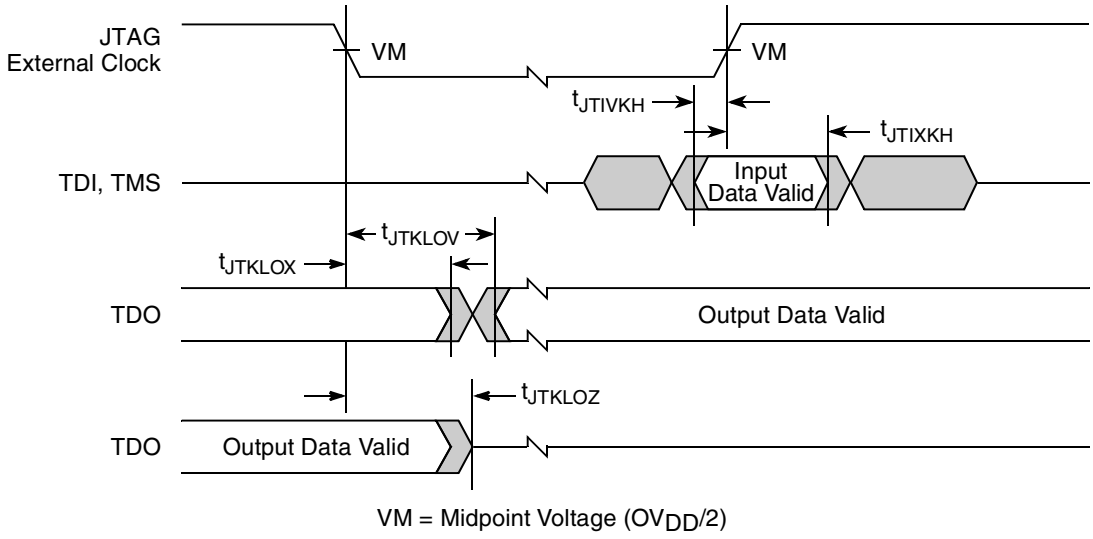


Figure 32. Test Access Port Timing Diagram

Figure 38 provides the AC test load for the timers.

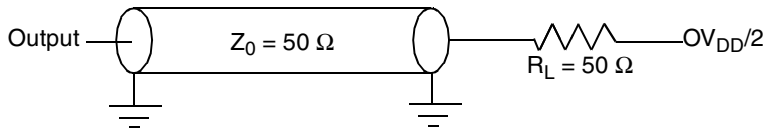


Figure 38. Timers AC Test Load

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the MPC8358E.

14.1 GPIO DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the device GPIO.

Table 50. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA	—

Note: This specification applies when operating from 3.3-V supply.

14.2 GPIO AC Timing Specifications

Table 51 provides the GPIO input and output AC timing specifications.

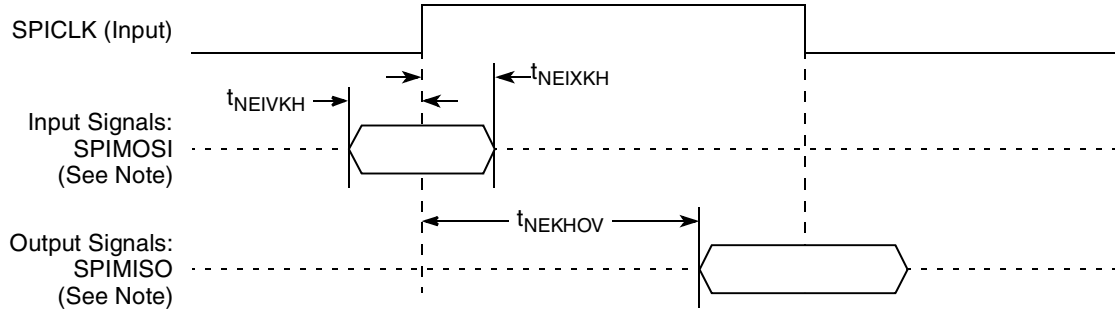
Table 51. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

Figure 41 and Figure 42 represent the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

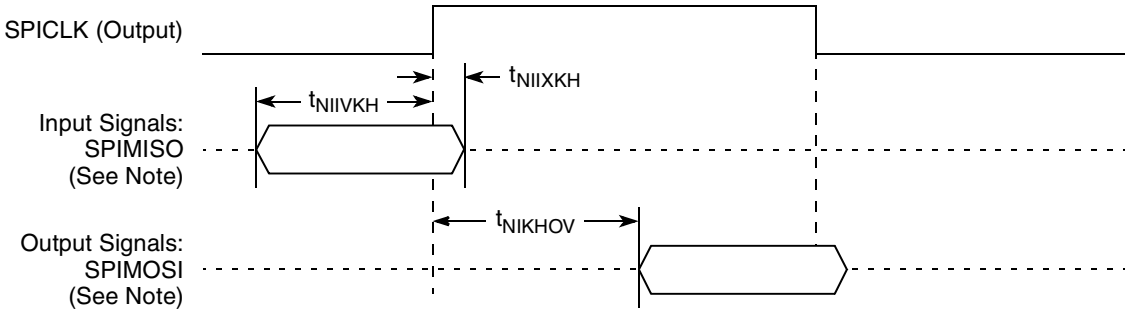
Figure 41 shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 41. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 42 shows the SPI timing in Master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 42. SPI AC Timing in Master Mode (Internal Clock) Diagram

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8358E.

17.1 TDM/SI DC Electrical Characteristics

Table 56 provides the DC electrical characteristics for the device TDM/SI.

Table 56. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V

4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement must exclude any effect of mark on top surface of package.
6. Distance from the seating plane to the encapsulant material.

21.3 Pinout Listings

Refer to AN3097, “MPC8360/MPC8358E PowerQUICC Design Checklist,” for proper pin termination and usage.

Table 65 shows the pin list of the MPC8358E PBGA package.

Table 65. MPC8358E PBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR SDRAM Memory Controller Interface				
MEMC_MDQ[0:63]	AD20, AG24, AF24, AH24, AF23, AE22, AH26, AD21, AH25, AD22, AF27, AB24, AG25, AC22, AE25, AC24, AD25, AB25, AC25, AG28, AD26, AE23, AG26, AC26, AD27, V25, AA28, AA25, Y26, W27, U24, W24, E28, H24, E26, D25, G27, H25, G26, F26, F27, F25, D26, F24, G25, E27, D27, C28, C27, F22, B26, F21, B28, E22, D24, C24, A25, E20, F20, D20, A23, C21, C23, E19	I/O	GV_{DD}	—
MEMC_MECC[0:7]	N26, N24, J26, H28, N28, P24, L26, K24	I/O	GV_{DD}	—
MEMC_MDM[0:8]	AG23, AD23, AE26, V28, G28, D28, D23, B24, U27	O	GV_{DD}	—
MEMC_MDQS[0:8]	AH23, AH27, AF28, T28, H26, E25, B25, A24, R28	I/O	GV_{DD}	—
MEMC_MBA[0:2]	V26, W28, Y28	O	GV_{DD}	—
MEMC_MA[0:14]	L25, M25, M24, K28, P28, T24, M27, R25, P25, L28, U26, M28, L27, K27, H27	O	GV_{DD}	—
MEMC_MODT[0:3]	AE21, AC19, E23, B23	—	GV_{DD}	6
$\overline{\text{MEMC\_MWE}}$	R27	O	GV_{DD}	—
$\overline{\text{MEMC\_MRAS}}$	W25	O	GV_{DD}	—
$\overline{\text{MEMC\_MCAS}}$	R24	O	GV_{DD}	—
$\overline{\text{MEMC\_MCS}}$[0:3]	T26, U28, J25, F28	O	GV_{DD}	—
MEMC_MCKE[0:1]	AD24, AE28	O	GV_{DD}	—
MEMC_MCK[0:5]	AG22, AG27, A26, C26, P26, E21	O	GV_{DD}	—
$\overline{\text{MEMC\_MCK}}$[0:5]	AF22, AF26, A27, B27, N27, D22	O	GV_{DD}	—
MDIC[0:1]	F19, AA27	I/O	GV_{DD}	11
PCI				
$\overline{\text{PCI\_INTA}}$/ PF[5]	R3	I/O	$LV_{DD}2$	2
$\overline{\text{PCI\_RESET\_OUT}}$/ PF[6]	P6	I/O	$LV_{DD}2$	—
PCI_AD[0:31]/ PG[0:31]	AB5, AC5, AG1, AA5, AF2, AD4, Y6, AF1, AE2, AC4, AD3, AE1, Y4, AC3, AD2, AD1, AB2, Y3, AA1, Y1, W1, V6, W3, V4, T5, W2, V5, V1, U4, V2, U2, T2	I/O	$LV_{DD}2$	—
$\overline{\text{PCI\_C\_BE}}$[0:3]/ PF[7:10]	Y5, AC2, Y2, U5	I/O	OV_{DD}	—

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TDI	AE8	I	OV_{DD}	4
TDO	AG7	O	OV_{DD}	3
TMS	AH7	I	OV_{DD}	4
$\overline{\text{TRST}}$	AG8	I	OV_{DD}	4
Test				
TEST	AF9	I	OV_{DD}	7
$\overline{\text{TEST\_SEL}}$	AE27	I	GV_{DD}	9
PMC				
$\overline{\text{QUIESCE}}$	AF4	O	OV_{DD}	—
System Control				
$\overline{\text{PORESET}}$	AE9	I	OV_{DD}	—
$\overline{\text{HRESET}}$	AG9	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	AH10	I/O	OV_{DD}	2
Thermal Management				
THERM0	K25	I	GV_{DD}	—
THERM1	AA26	I	GV_{DD}	—
Power and Ground Signals				
$AV_{DD}1$	AF8	Power for LBIU DLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	AH8	Power for CE PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}5$	AB26	Power for e300 PLL (1.2 V)	$AV_{DD}5$	—
$AV_{DD}6$	AH9	Power for system PLL (1.2 V)	$AV_{DD}6$	—
GND	C16, D11, D21, E24, F7, J10, J12, J15, J16, J17, J28, K11, K13, K14, K17, K18, L4, L9, L11, L12, L13, L14, L15, L16, L17, L18, L19, L24, M10, M11, M14, M15, M18, M19, N11, N18, N25, P9, P11, P18, P19, R9, R11, R14, R15, R18, R19, R26, T10, T11, T14, T15, T18, T25, U10, U11, U18, V9, V11, V14, V15, V18, V24, V27, W18, W19, Y11, Y14, Y18, Y19, Y25, Y27, AB4, AB27, AC27, AE20, AE24, AF5, AF15, AG10	—	—	—

input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCIOEN*n*] parameters enable the PCI_CLK_OUT*n*, respectively.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the device to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock. When the device is configured as a PCI agent device the CLKIN and the CFG_CLKIN_DIV signals should be tied to GND.

When the device is configured as a PCI host device (RCWH[PCIHOST] = 1) and PCI clock output is disabled (RCWH[PCICKDRV] = 0), clock distribution and balancing done externally on the board. Therefore, PCI_SYNC_IN is the primary input clock.

As shown in Figure 53, the primary clock input (frequency) is multiplied by the QUICC Engine block phase-locked loop (PLL), the system PLL, and the clock unit to create the QUICC Engine clock (*ce_clk*), the coherent system bus clock (*csb_clk*), the internal DDRC1 controller clock (*ddr1_clk*), and the internal clock for the local bus interface unit and DDR2 memory controller (*lb_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb\_clk = \{PCI\_SYNC\_IN \times (1 + CFG\_CLKIN\_DIV)\} \times SPMF$$

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency; in PCI agent mode, CFG_CLKIN_DIV must be pulled down (low), so PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the PCI_CLK frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies up the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL) which is loaded at power-on reset or by one of the hard-coded reset options. See Chapter 4, “Reset, Clocking, and Initialization,” in the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for more information on the clock subsystem.

The *ce_clk* frequency is determined by the QUICC Engine PLL multiplication factor (RCWL[CEPMF) and the QUICC Engine PLL division factor (RCWL[CEPDF]) according to the following equation:

$$ce\_clk = (\text{primary clock input} \times CEPMF) \div (1 + CEPDF)$$

The internal *ddr1_clk* frequency is determined by the following equation:

$$ddr1\_clk = csb\_clk \times (1 + RCWL[DDR1CM])$$

Note that the lb_clk clock frequency (for DDRC2) is determined by RCWL[LBCM]. The *internal ddr1_clk* frequency is not the external memory bus frequency; *ddr1_clk* passes through the DDRC1 clock divider (÷2) to create the differential DDRC1 memory bus clock outputs (MEMC1_MCK and $\overline{\text{MEMC1\_MCK}}$). However, the data rate is the same frequency as *ddr1_clk*.

The internal *lb_clk* frequency is determined by the following equation:

$$lb\_clk = csb\_clk \times (1 + RCWL[LBCM])$$

Table 70. CSB Frequency Options (continued)

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk*: Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
High	0110	6:1			200	
High	0111	7:1			233	
High	1000	8:1				
High	1001	9:1				
High	1010	10:1				
High	1011	11:1				
High	1100	12:1				
High	1101	13:1				
High	1110	14:1				
High	1111	15:1				
High	0000	16:1				

1 CFG_CLKIN_DIV is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV must be pulled down (low) in agent mode.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

22.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 71 shows the encodings for RCWL[COREPLL]. COREPLL values not listed in Table 71 should be considered reserved.

Table 71. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk*:*csb_clk* Ratio	VCO divider
0–1	2–5	6		
nn	**0000**	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	**0001**	0	1:1	÷2
01	**0001**	0	1:1	÷4
10	**0001**	0	1:1	÷8
11	**0001**	0	1:1	÷8
00	**0001**	1	1.5:1	÷2
01	**0001**	1	1.5:1	÷4
10	**0001**	1	1.5:1	÷8

Table 71. e300 Core PLL Configuration (continued)

RCWL[COREPLL]			*core_clk*:*csb_clk* Ratio	VCO divider
0–1	2–5	6		
11	0001	1	1.5:1	÷8
00	0010	0	2:1	÷2
01	0010	0	2:1	÷4
10	0010	0	2:1	÷8
11	0010	0	2:1	÷8
00	0010	1	2.5:1	÷2
01	0010	1	2.5:1	÷4
10	0010	1	2.5:1	÷8
11	0010	1	2.5:1	÷8
00	0011	0	3:1	÷2
01	0011	0	3:1	÷4
10	0011	0	3:1	÷8
11	0011	0	3:1	÷8

NOTE

Core VCO frequency = Core frequency × VCO divider. The VCO divider (RCWL[COREPLL[0:1]]) must be set properly so that the core VCO frequency is in the range of 800–1800 MHz. Having a core frequency below the CSB frequency is not a possible option because the core frequency must be equal to or greater than the CSB frequency.

22.3 QUICC Engine Block PLL Configuration

The QUICC Engine block PLL is controlled by the RCWL[CEPMF], RCWL[CEPDF], and RCWL[CEVCOD] parameters. Table 72 shows the multiplication factor encodings for the QUICC Engine block PLL.

Table 72. QUICC Engine Block PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000	0	× 16
00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4

Table 72. QUICC Engine Block PLL Multiplication Factors (continued)

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
01011	1	× 5.5
01101	1	× 6.5
01111	1	× 7.5
10001	1	× 8.5
10011	1	× 9.5
10101	1	× 10.5
10111	1	× 11.5
11001	1	× 12.5
11011	1	× 13.5
11101	1	× 14.5

Note:
1. Reserved modes are not listed.

The RCWL[CEVCOD] denotes the QUICC Engine Block PLL VCO internal frequency as shown in Table 73.

Table 73. QUICC Engine Block PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine block VCO frequency is in the range of 600–1400 MHz. The QUICC Engine block frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine block frequencies should be selected according to the performance requirements.

The QUICC Engine block VCO frequency is derived from the following equations:

ce_clk = (primary clock input × CEPMF) ÷ (1 + CEPDF)

QE VCO Frequency = *ce_clk* × VCO divider × (1 + CEPDF)

23.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

23.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package will be approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device. At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JA}$ = junction to board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.